

**In The Claims:**

The listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. (currently amended) An integrated circuit device comprising:
  - a substrate;
  - a first conductive electrode on the substrate, the first conductive electrode having an electrode wall extending away from the substrate;
  - an insulating spacer on the electrode wall wherein portions of the electrode wall are free of the insulating spacer between the substrate and the insulating spacer, and wherein portions of the electrode most distant from the substrate are free of the insulating spacer;
  - a capacitor dielectric layer on portions of the electrode wall free of the spacer between the substrate and the insulating spacer; and
  - a second conductive electrode on the capacitor dielectric layer opposite the electrode wall between the substrate and the insulating spacer, wherein a thickness of the insulating spacer between the first and second conductive electrodes is greater than a thickness of the capacitor dielectric layer between the first and second conductive electrodes;

wherein the electrode wall includes a recessed portion and wherein the insulating spacer is on the recessed portion of the electrode wall.
2. (original) An integrated circuit device according to Claim 1 wherein the capacitor dielectric layer and the insulating spacer comprise different materials.
3. (original) An integrated circuit device according to Claim 1 further comprising:
  - a transistor on the substrate;
  - an insulating layer between the substrate and the first conductive electrode; and

a conductive plug providing electrical coupling between the first conductive electrode and a source/drain region of the transistor through the insulating layer.

4. (original) An integrated circuit device according to Claim 1 wherein portions of the electrode wall extend beyond the spacer away from the substrate free of the insulating spacer, and wherein the capacitor dielectric layer is also on portions of the electrode wall extending beyond the spacer.

Claims 5-79 (canceled).

80. (currently amended) An electronic integrated circuit device according to Claim 1 wherein the capacitor dielectric layer is directly on the portions of the electrode most distant from the substrate that are free of the insulating spacer.